SKT 80

THYRISTOR BRIDGE,SCR BRIDGE

Stud Thyristor

Line Thyristor

SKT 80

Features

- Hermetic metal case with glass insulator
- Threaded stud ISO M12 or UNF 1/2-20
- International standard case

Typical Applications*

- DC motor control (e. g. for machines tools)
- Controlled rectifiers (e. g. for battery charging)
- AC controllers (e. g. for temperature control)
- Recommended snubber network e. g. for $V_{VRMS} \leq 400$ V: R = 47 Ω/10 W, C = 0,22 µF

1) Available with UNF thread 1/2-20 UNF2A, e. g. SKT 80/06D UNF

V_{RSM} V	V_{RRM}, V_{DRM} V	I_{TRMS} = 135 A (maximum value for continuous operation) I_{TAV} = 80 A (sin. 180; T_c = 85 °C)
700	600	SKT 80/06D[1)]
900	800	SKT 80/08D
1300	1200	SKT 80/12E[1)]
1500	1400	SKT 80/14E
1700	1600	SKT 80/16E[1)]
1900	1800	SKT 80/18E

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; T_c = 100 (85) °C;	60 (80)	A
I_D	K1,1; T_a = 45 °C; B2 / B6	76 / 105	A
	K0,55; T_a = 45 °C; B2 / B6	110 /150	A
I_{RMS}	K1,1; T_a = 45 °C; W1C	84	A
I_{TSM}	T_{vj} = 25 °C; 10 ms	1700	A
	T_{vj} = 130 °C; 10 ms	1500	A
i²t	T_{vj} = 25 °C; 8,35 ... 10 ms	14500	A²s
	T_{vj} = 130 °C; 8,35 ... 10 ms	11000	A²s
V_T	T_{vj} = 25 °C; I_T = 300 A	max. 2,25	V
$V_{T(TO)}$	T_{vj} = 130 °C	max. 1,2	V
r_T	T_{vj} = 130 °C	max. 4	mΩ
I_{DD}; I_{RD}	T_{vj} = 130 °C; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}	max. 30	mA
t_{gd}	T_{vj} = 25 °C; I_G = 1 A; di_G/dt = 1 A/µs	1	µs
t_{gr}	V_D = 0,67 * V_{DRM}	2	µs
$(di/dt)_{cr}$	T_{vj} = 130 °C	max. 50	A/µs
$(dv/dt)_{cr}$	T_{vj} = 130 °C ; SKT ...D / SKT ...E	max. 500 / 1000	V/µs
t_q	T_{vj} = 130 °C ,	100	µs
I_H	T_{vj} = 25 °C; typ. / max.	150 / 250	mA
I_L	T_{vj} = 25 °C; typ. / max.	300 / 600	mA
V_{GT}	T_{vj} = 25 °C; d.c.	min. 3	V
I_{GT}	T_{vj} = 25 °C; d.c.	min. 150	mA
V_{GD}	T_{vj} = 130 °C; d.c.	max. 0,25	V
I_{GD}	T_{vj} = 130 °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.	0,25	K/W
$R_{th(j-c)}$	sin. 180	0,28	K/W
$R_{th(j-c)}$	rec. 120	0,31	K/W
$R_{th(c-s)}$		0,08	K/W
T_{vj}		- 40 ... + 130	°C
T_{stg}		- 55 ... + 150	°C
V_{isol}		-	V~
M_s	to heatsink	10	Nm
a		5 * 9,81	m/s²
m	approx.	100	g
Case		B 5	

SKT

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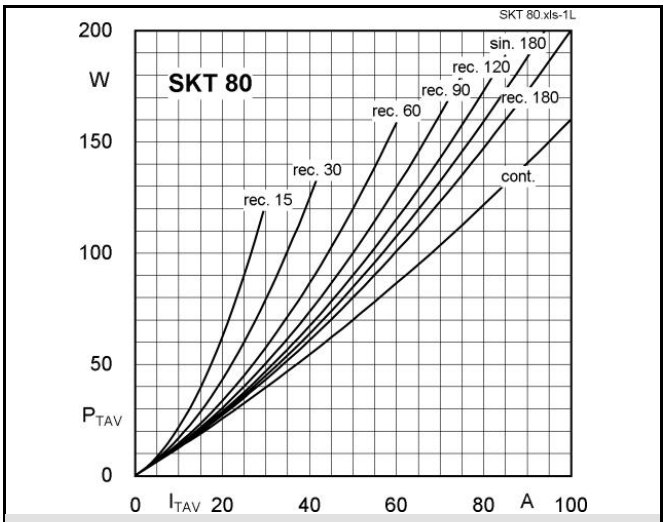

Fig. 1L Power dissipation vs. on-state current

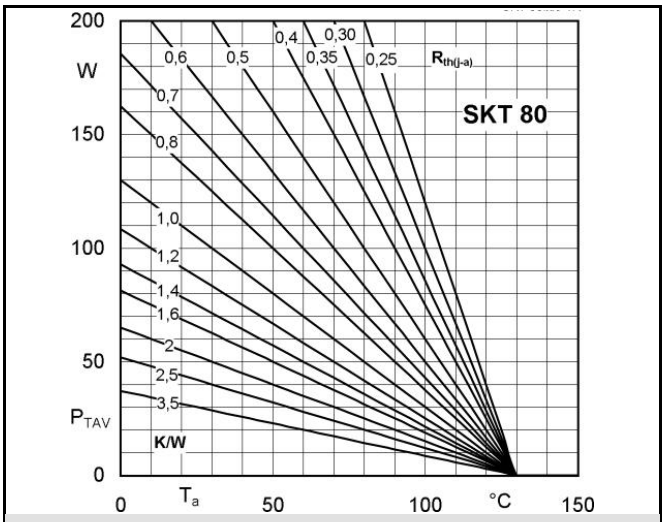

Fig. 1R Power dissipation vs. ambient temperature

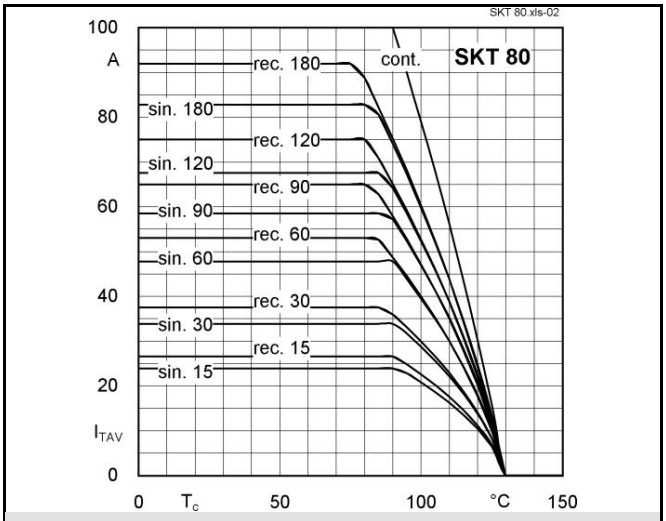

Fig. 2 Rated on-state current vs. case temperature

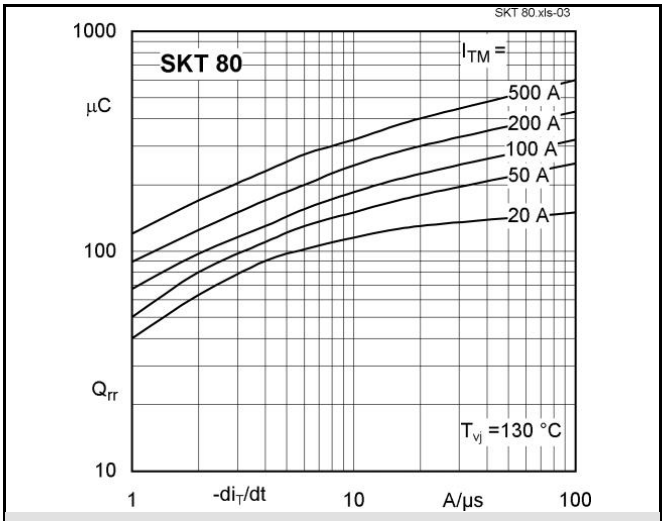

Fig. 3 Recovered charge vs. current decrease

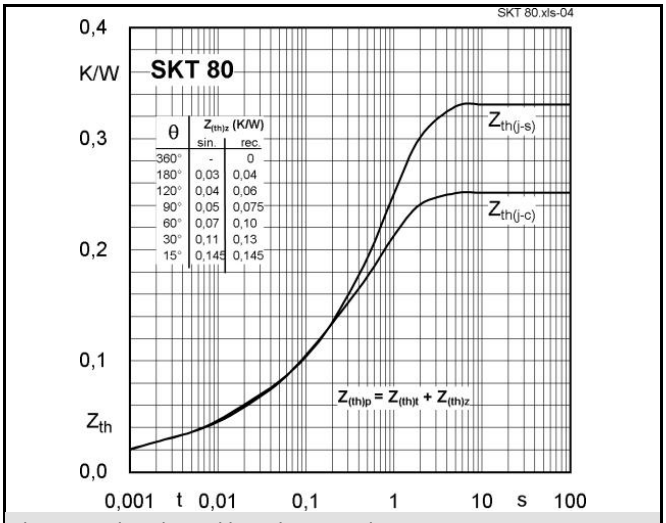

Fig. 4 Transient thermal impedance vs. time

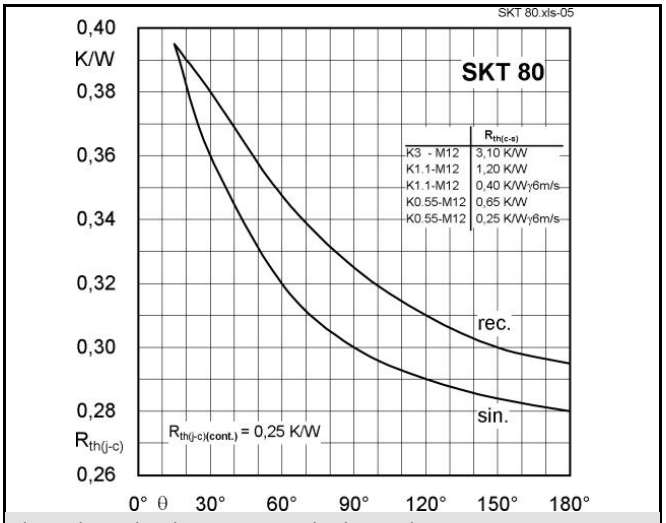

Fig. 5 Thermal resistance vs. conduction angle

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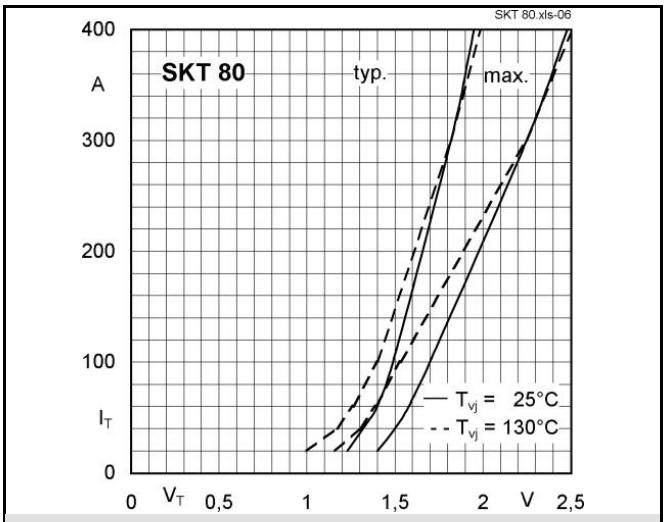

Fig. 6 On-state characteristics

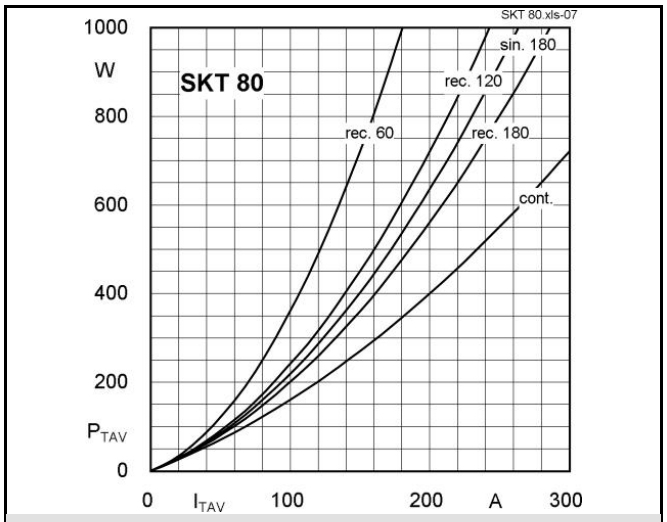

Fig. 7 Power dissipation vs. on-state current

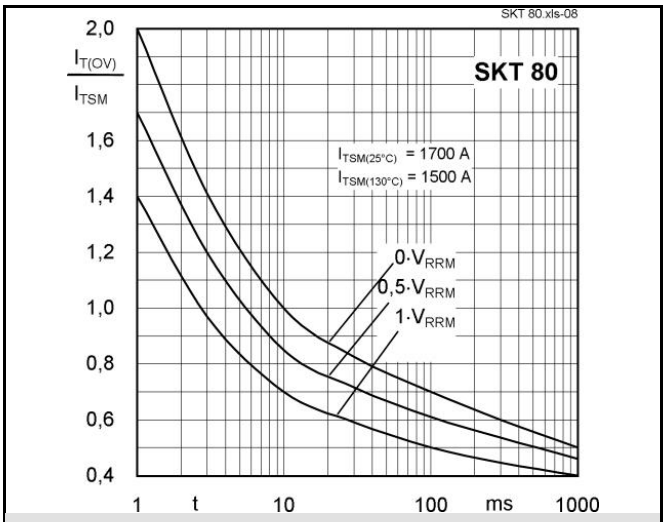

Fig. 8 Surge overload curent vs. time

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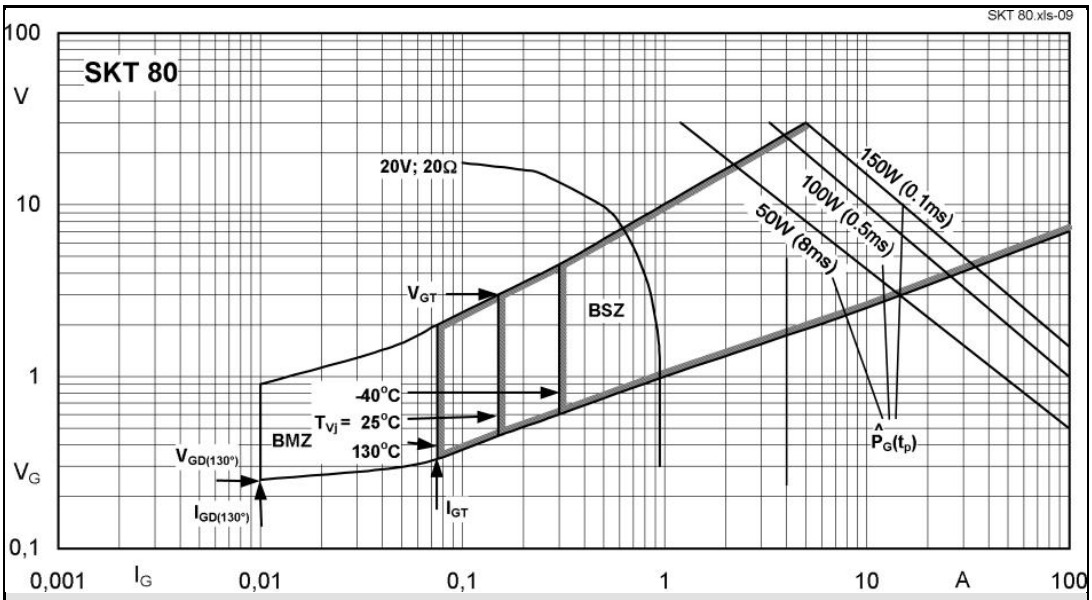
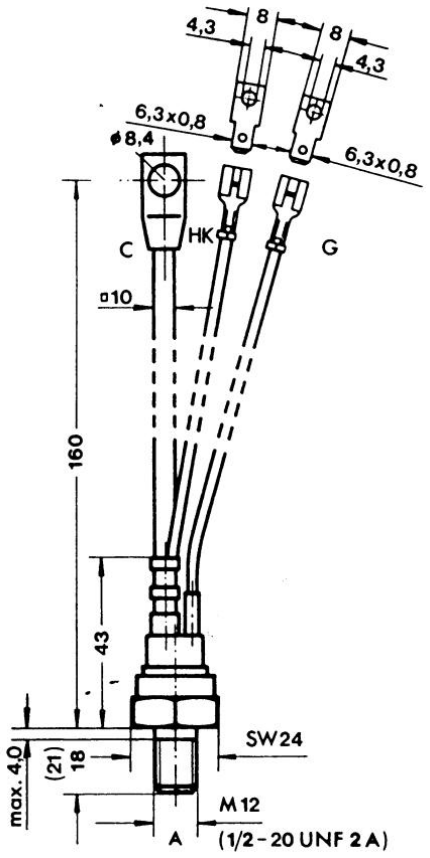


Fig. 9 Gate trigger characteristics

Dimensions in mm



Case B 5 (IEC 60191-2: A12MA, A12U; JEDEC: TO-209 (TO-94))

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON

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products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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